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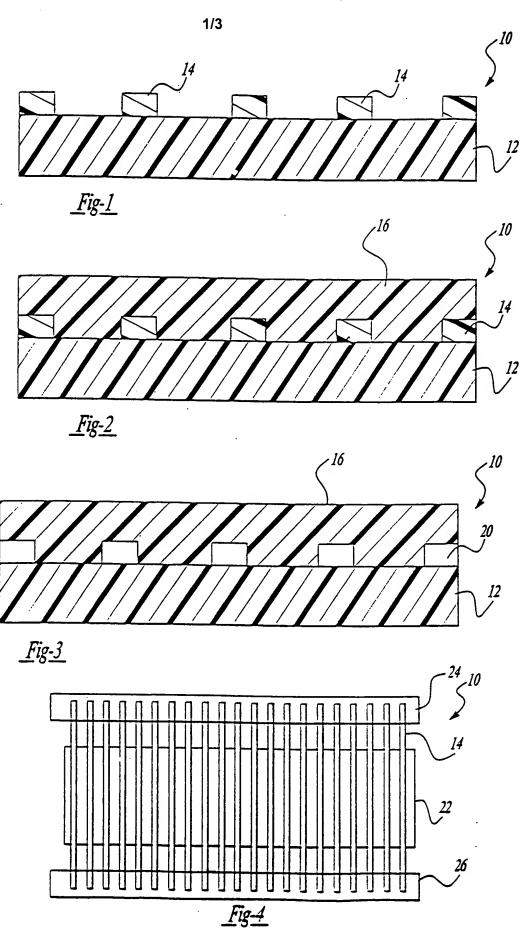
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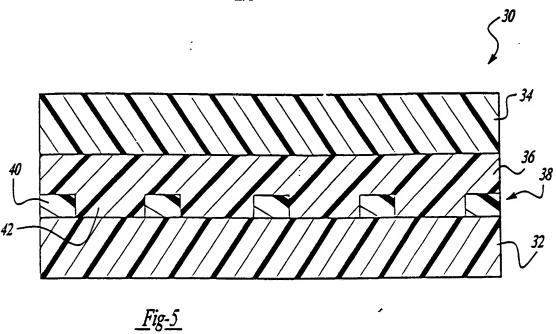
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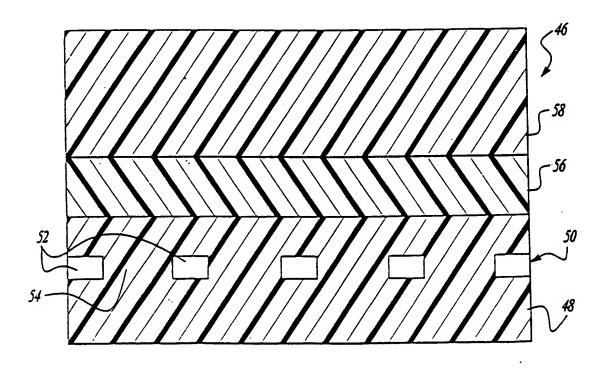
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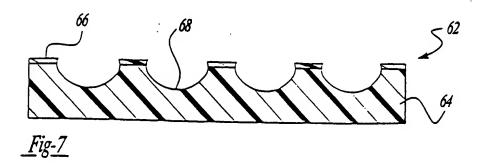
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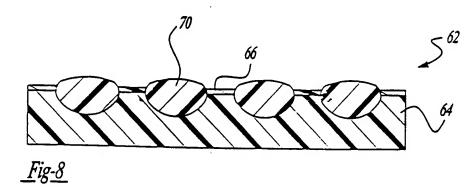


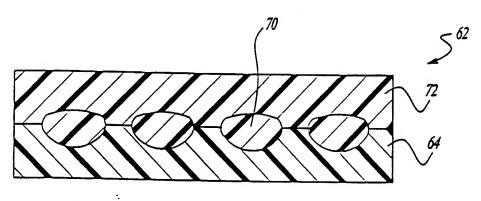


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<u>Fig-9</u>

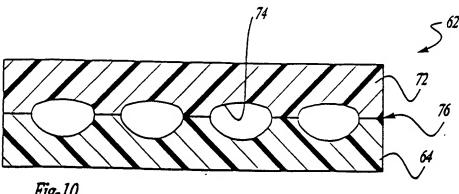


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